

Rev.B Jul.-2026

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TO-220 .> // x N ?ú 3 « | • 'ož

N-CHANNEL MOSFET in a TO-220 Plastic Package.

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$V_{DS} (V) = 100V$ $I_D = 130A (V_{GS} = f 20V)$

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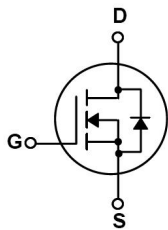
—)í D }ož HF Product.

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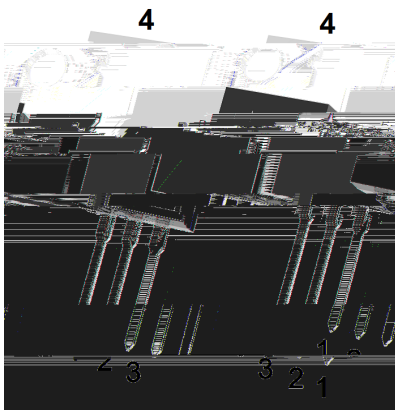
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Motor drivers, DC - DC Converter.

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PIN1 y G

PIN 2o•4 y D

PIN 3 y S

, M V

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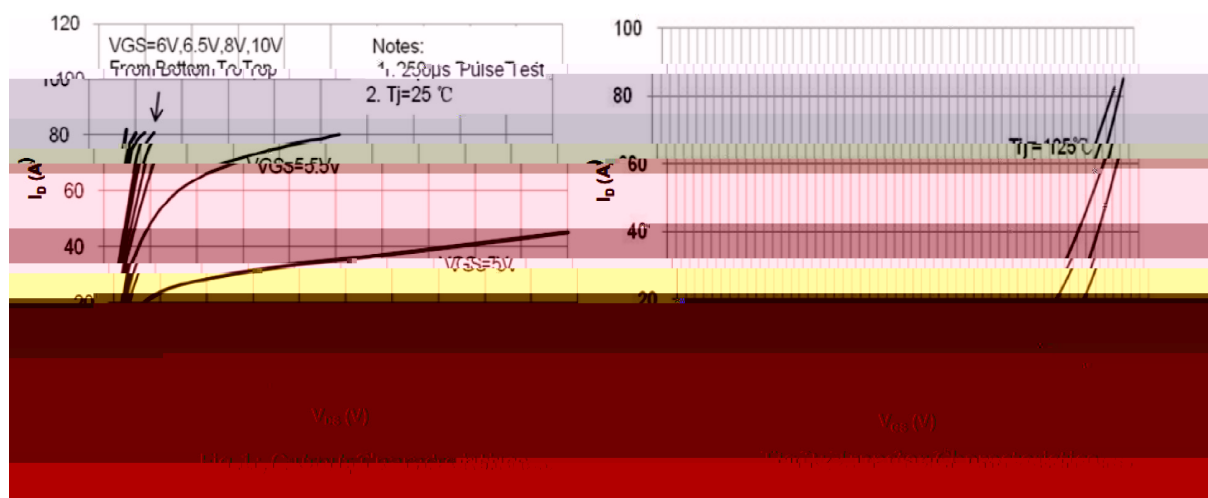
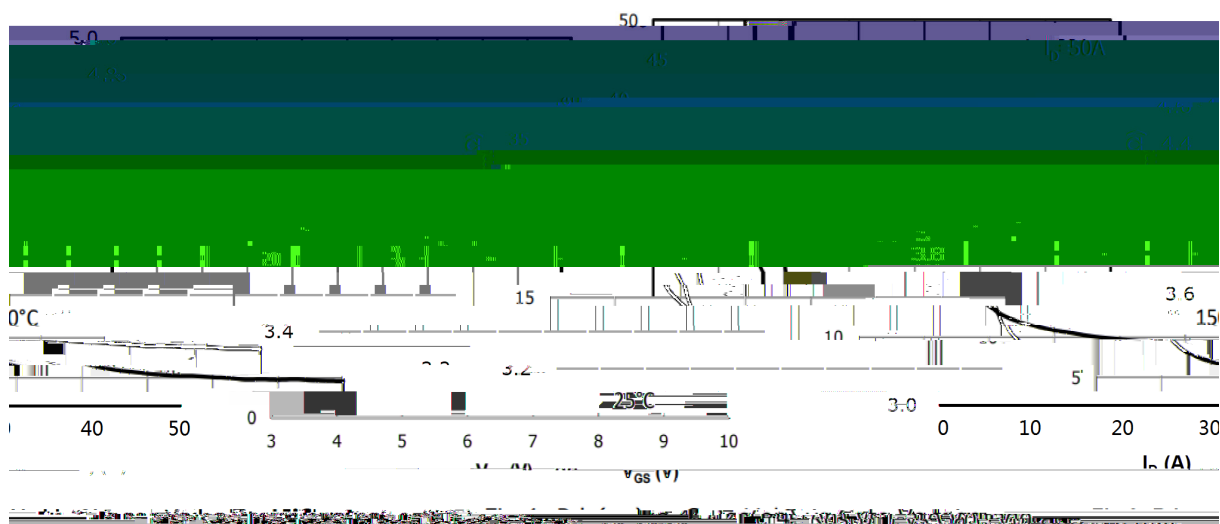
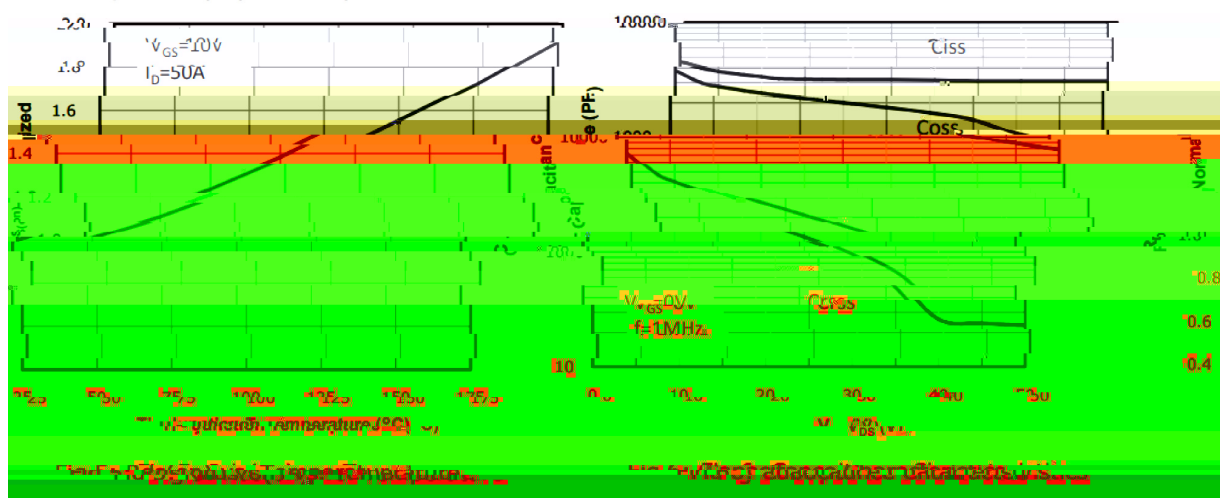
See Marking Instructions.

@ f Parameter	... Z Symbol	f > Rating	% y Unit
Drain-Source Voltage	V _{DSS}	100	V
Drain Current	I _D (T _c =25 °C)	130	A
	I _D (T _c =100 °C)	85	A
Pulsed Drain Current	I _{DM}	480	A
Gate-Source Voltage	V _{GS}	f 20	V
Single Pulsed Avalanche Energy(L=0.3mH)	E _{AS}	430	mJ
Total Power Dissipation	P _D (T _c =25 °C)	178	W
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	-
Thermal Resistance-Junction to Ambient**	R _{JA}	64	- /W
Thermal Resistance-Junction to Case	R _{JC}	0.7	

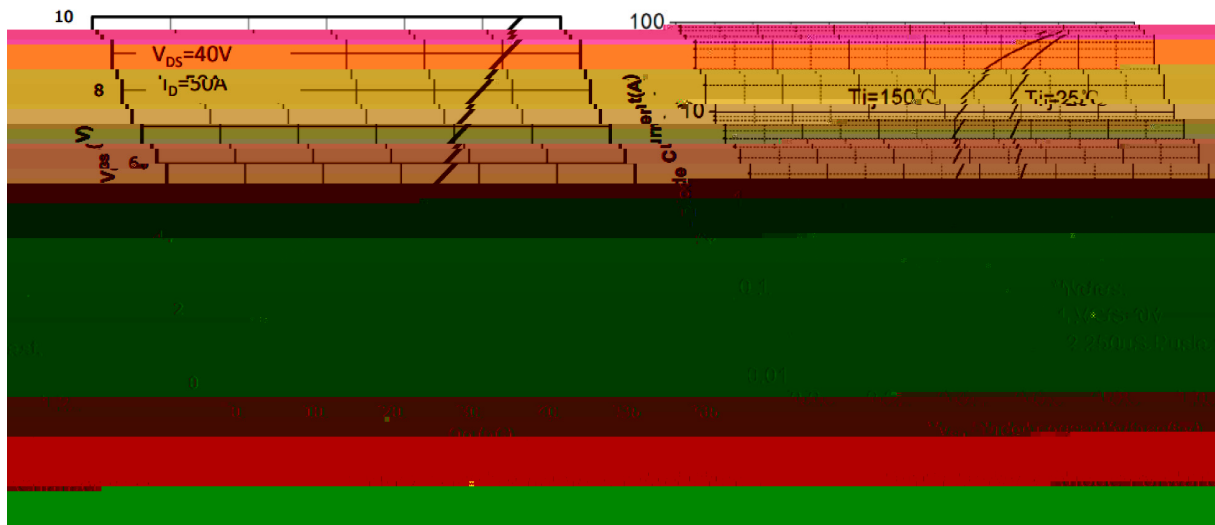
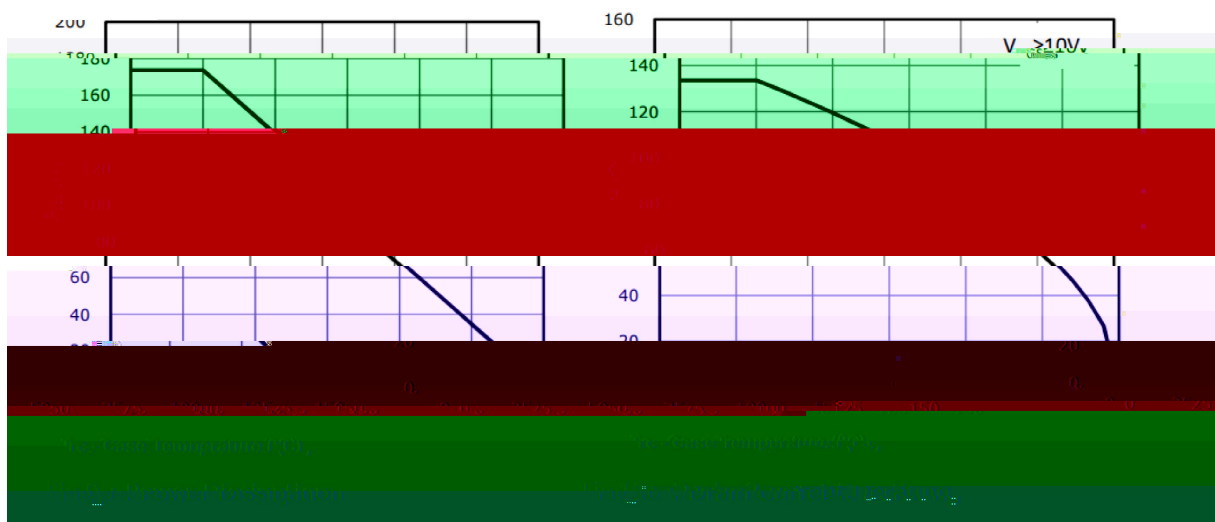
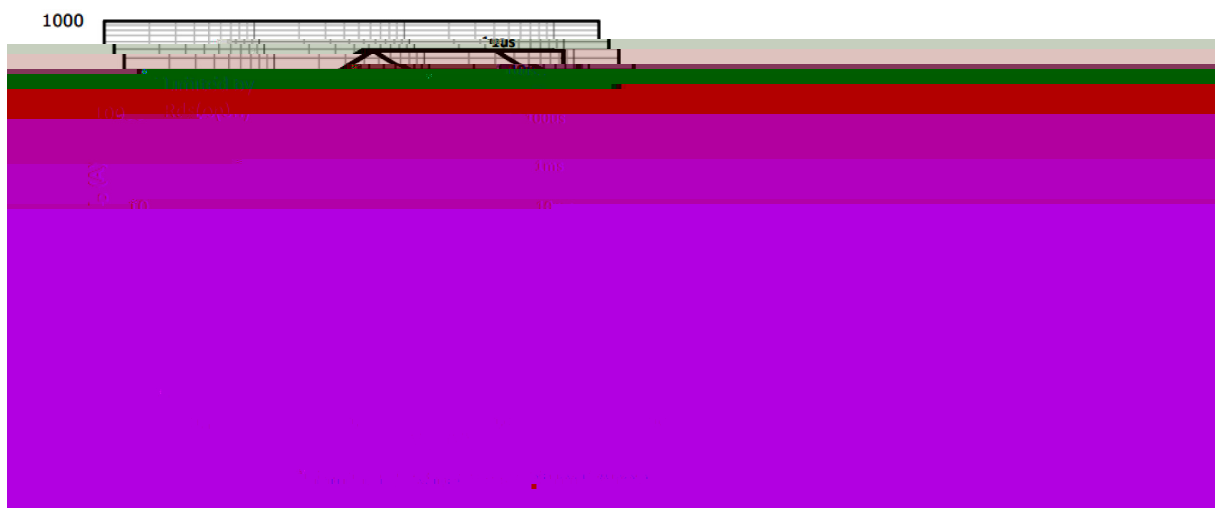
@ f Parameter	... Z Symbol	y i Ú ^ Test Conditions	Â 4 > Min	Á ° > Typ	Â Ý > Max	% y Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250 A	100			V
Drain Leakage Current	I _{DSS}	V _{DS} =100V V _{GS} =0V			1	A
Gate Leakage Current	I _{GSS}	V _{GS} =±20V V _{DS} =0V				

@ f Parameter	... Z Symbol	y i Ú ^ Test Conditions	Â 4 › Min	Á ° › Typ	Â Ý › Max	% y Unit
Turn-On Delay Time	t					

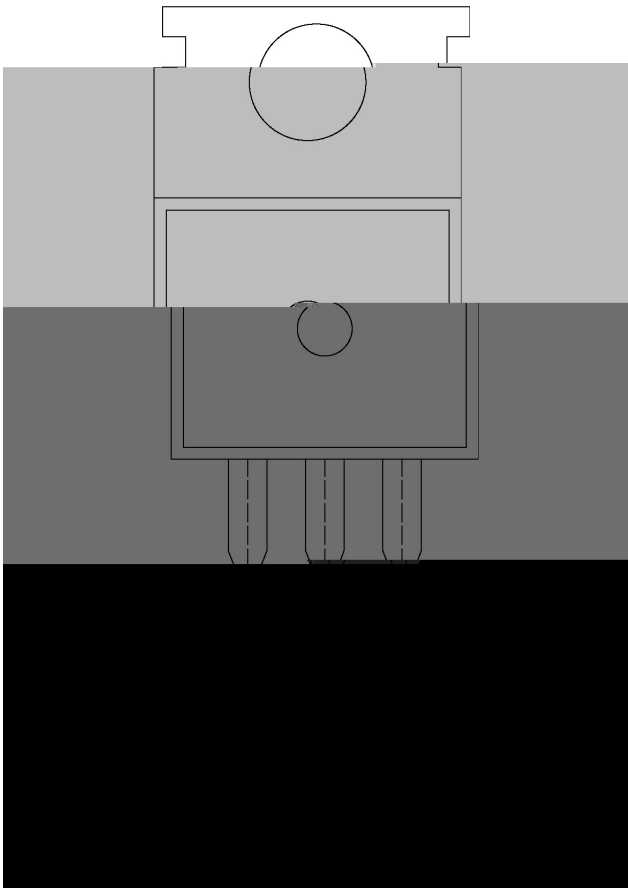
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y ŷ D Z W A k š ŷ D Z J
4 9 . y ° Z W A

Note:
BR: Company Code
****: Lot No. Code, code change with Lot No.

GPD t... • Ž Ć x /

a Ć y

1o• Ä ½ “† 25 ½150 - k ž • 60 ½90sec;

2o• Q > “† 255 r5 - k ž • 4 Ò 5 r0.5sec;

3o•D N ò i Ò 0, † 2 ½10 - /sec.

Note:

1.Preheating:25~150 - , Time:60~90sec.

2.Peak Temp.:255 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »]

“† y 270 r5 -

ž • y 10 r1 sec.

Temp.:270±5

Time:10±1 sec

GP á

• ^ x / BULK

 Package Type
 7>û ~ E

Units ;>û !H

Dimension ;>û p . (unit Åmm³)